

## P-Channel 20V (D-S) MOSFET

### General Description

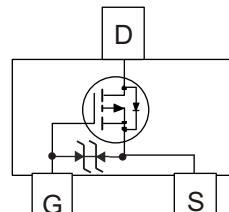
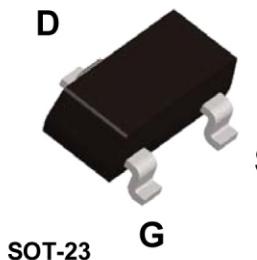
This miniature surface mount MOSFET uses advanced Trench process, low  $R_{DS(on)}$  assures minimal power loss and energy convert, which makes this device ideal for use in power management circuit.

### Applications

- Load switching
- Low current DC-DC converters
- Small power management

### Features

- $V_{DS}(V) = -20V$
- $I_D(A) = -5.3A(V_{GS} = -4.5V)$
- $R_{DS(on)} = 34 \text{ m}\Omega @ V_{GS} = -4.5V$
- $R_{DS(on)} = 48 \text{ m}\Omega @ V_{GS} = -2.5V$
- $R_{DS(on)} = 80 \text{ m}\Omega @ V_{GS} = -1.8V$
- ESD Rating : 3000V HBM
- Low gate charge
- Fast switching speed
- High performance trench technology



### Absolute Maximum Ratings ( $TA = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	
Continuous Drain Current <sup>a</sup>	$I_D$	-5.3	A
		-4.2	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	-21	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	-1	A
Power Dissipation <sup>a</sup>	$P_D$	1. 4	W
		1. 0	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	°C

### Thermal Resistance Ratings

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	90	°C/W
		130	



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MegaPower Semiconductor

MI3415

### Package Outlines and Ordering Information

Device	Device Marking	Reel Size	Tape Width	Quantity
MI3415	MPOS	7"	8mm	3000 units

### Specifications (TA = 25°C Unless Otherwise Noted)

Parameter	Symbol	Test Conditions	Limits			Units
			Min	Typ	Max	
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>D</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250 uA	-0. 5	-0. 8	-1	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>D</sub> =0V, V <sub>GS</sub> =±12V			±10	uA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>D</sub> =-20V, V <sub>GS</sub> =0V			-1	uA
		V <sub>D</sub> =-20V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C			-30	
On-State Drain Current <sup>c</sup>	I <sub>D(on)</sub>	V <sub>D</sub> =-5V, V <sub>GS</sub> =-4. 5V	-21			A
Drain-Source On-Resistance <sup>c</sup>	R <sub>D(S(on))</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5.3A		25	34	mΩ
		V <sub>GS</sub> =-2.5 V, I <sub>D</sub> =-2.5A		34	48	
		V <sub>GS</sub> =-1.8 V, I <sub>D</sub> =-2A		52	80	
Forward Transconductance <sup>c</sup>	g <sub>fS</sub>	V <sub>D</sub> =-5V, I <sub>D</sub> =-5.3A		21		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.75	-1. 3	V
<b>Dynamic</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>D</sub> =-10V, V <sub>GS</sub> =0V f=1MHz		1500		pF
Output Capacitance	C <sub>oss</sub>			220		
Reverse Transfer Capacitance	C <sub>rss</sub>			160		
<b>Switching</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>D</sub> =-10V, V <sub>GS</sub> =-4.5V I <sub>D</sub> =-5.3A		14	20	nC
Gate-Source Charge	Q <sub>gs</sub>			2.1		
Gate-Drain Charge	Q <sub>gd</sub>			4.7		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>D</sub> =-10V, I <sub>D</sub> =-2.2A, R <sub>G</sub> =6 ohm, V <sub>GEN</sub> =-4.5V		6	11	ns
Rise Time	t <sub>r</sub>			13	23	
Turn-Off Delay Time	t <sub>d(off)</sub>			86	145	
Fall-Time	t <sub>f</sub>			42	70	

- Notes: a. Surface Mounted on 1" x 1" FR4 Board.  
 b. Pulse width limited by maximum junction temperature  
 c. Pulse test: PW <= 300us duty cycle <= 2%.



### Typical Electrical and Thermal Characteristics

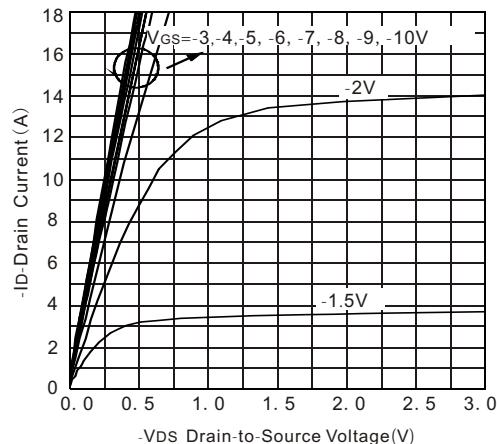


Figure 1: Output Characteristics

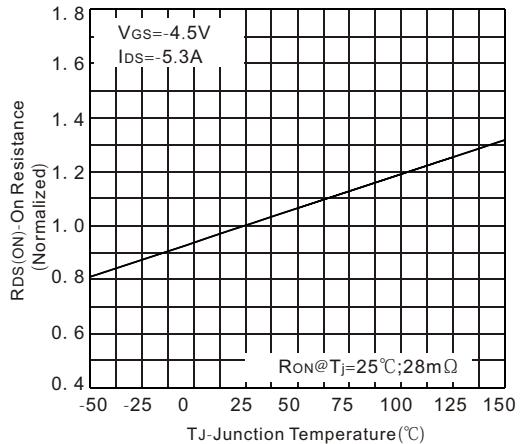


Figure 2: On-Resistance vs. Junction Temperature

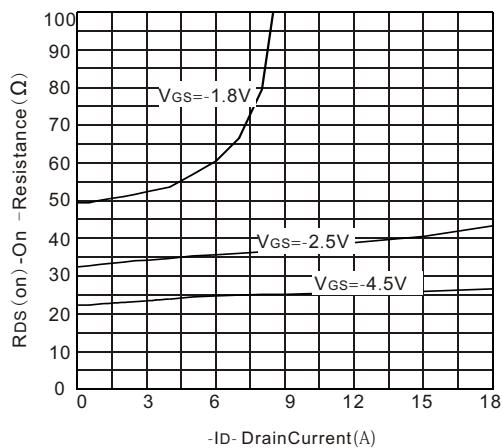


Figure 3: On-Resistance vs. Drain Current

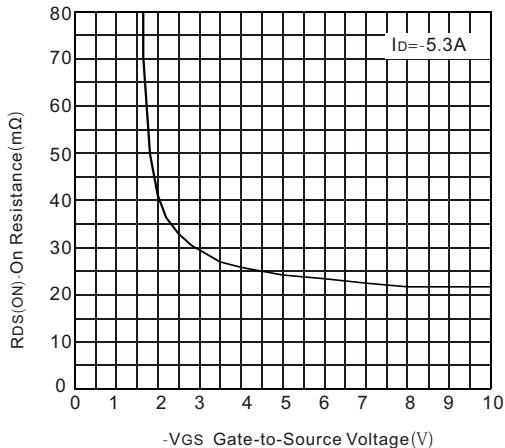


Figure 4: On-Resistance vs. Gate-to-Source Voltage

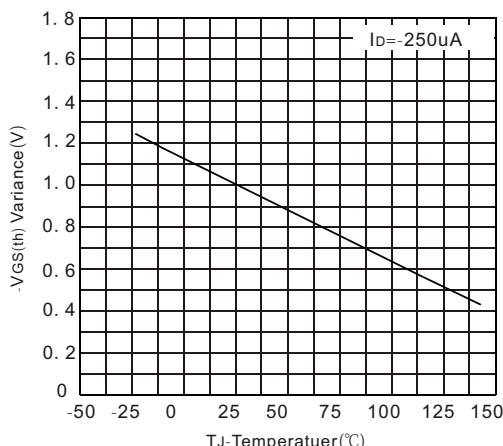


Figure 5: Threshold Voltage

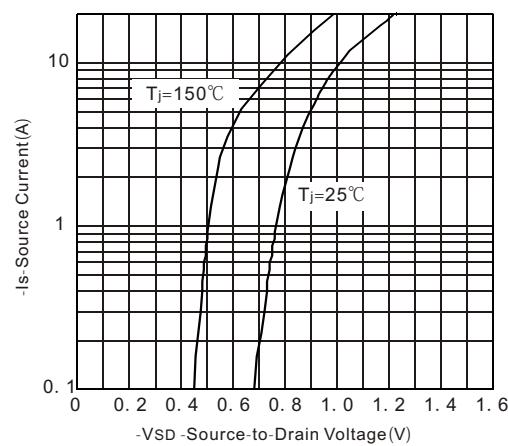


Figure 6: Source-Drain Diode Forward Voltage



### Typical Electrical and Thermal Characteristics

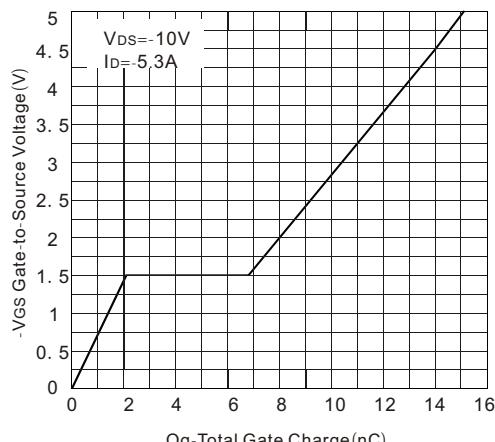


Figure 7 :Gate Change

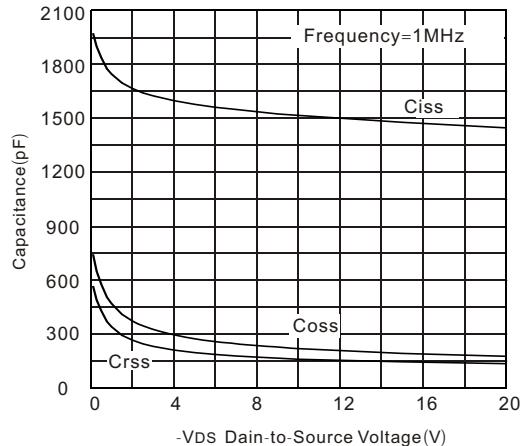


Figure 8: Capacitance

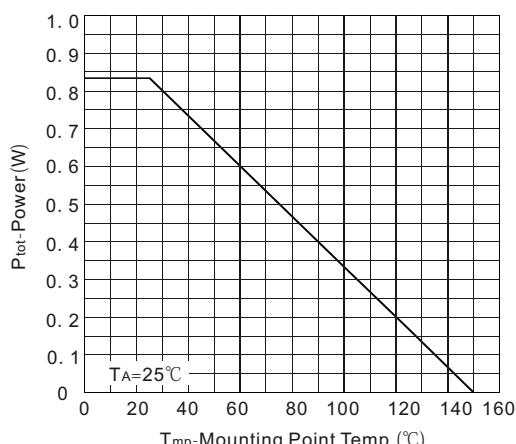


Figure 9: Power Capability

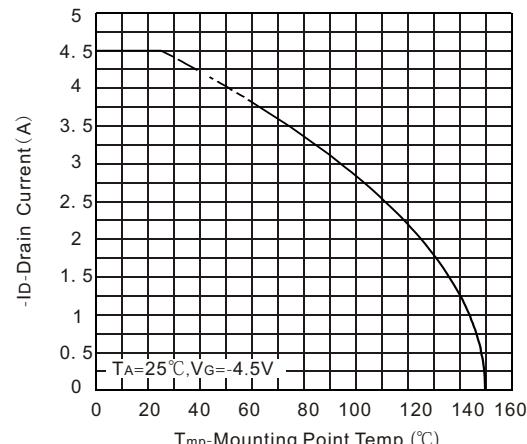


Figure 10: Current Capability

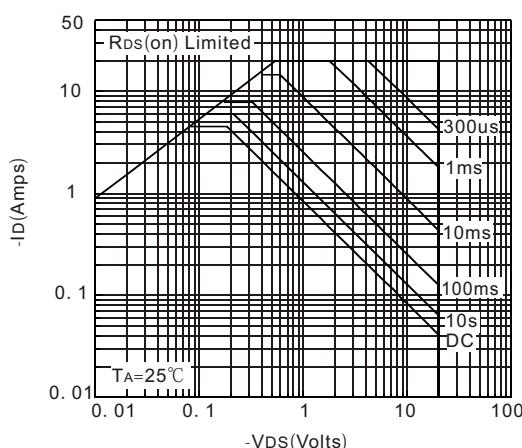


Figure 11:Maximum Forward Biased Safe Operating Area

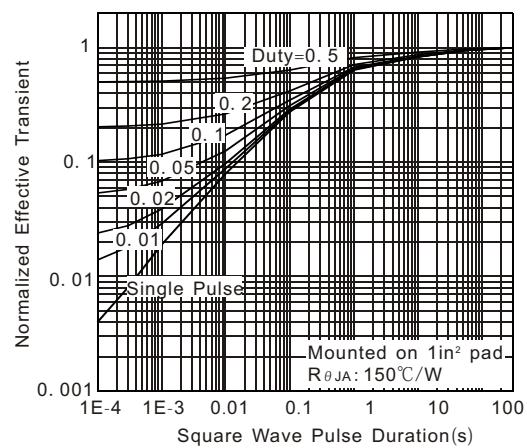
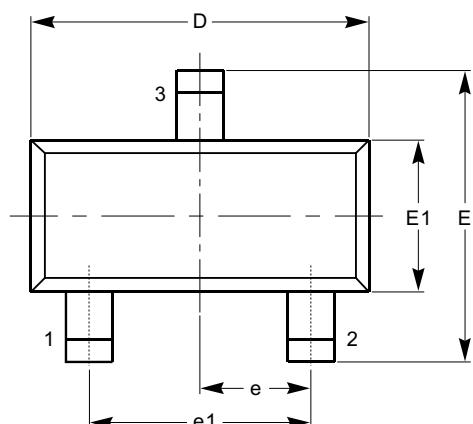


Figure 12:Transient Thermal Impedance



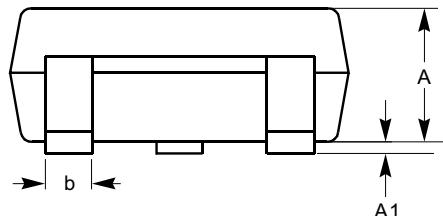
### Package Outline

#### SOT23\_3Lead

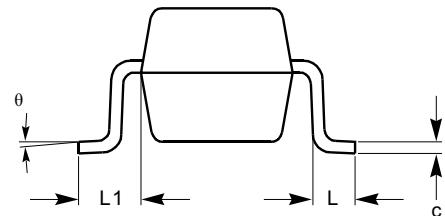


Unit: mm

Symbol	Min	Nom	Max
A	0.70	1.00	1.15
A1	0.00	---	0.13
b	0.30	0.40	0.50
c	0.08	0.13	0.20
D	2.80	2.90	3.10
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e	0.95 BSC		
e1	1.90 BSC		
L	0.40 REF		
L1	0.54 REF		
θ	0°	5°	8°



SIDE VIEW



END VIEW

#### Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Package body sizes exclude mold flash and gate burrs.
- (3) Complies with JEDEC TO-236.

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